

## Silicon Power Schottky Diode

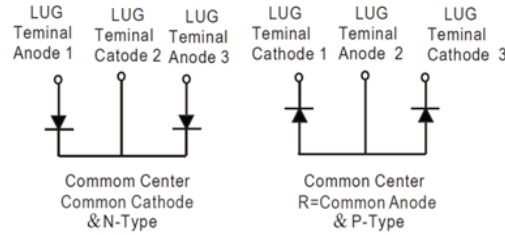
$V_{RRM} = 45\text{ V} - 100\text{ V}$

$I_{F(AV)} = 200\text{ A}$

### Features

- High Surge Capability
- Types from 45 V to 100 V  $V_{RRM}$
- Isolation Type Package
- Electrically Isolated Base Plate
- Not ESD Sensitive

Three Tower Package



Maximum ratings, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)

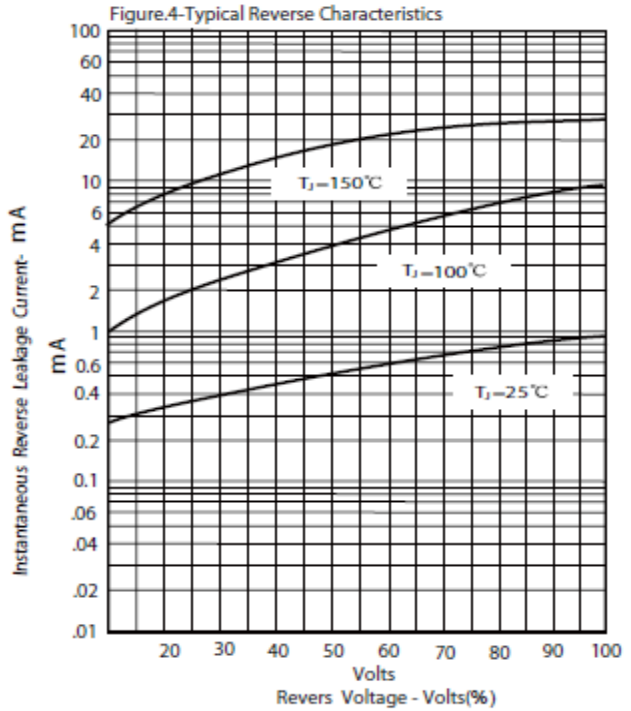
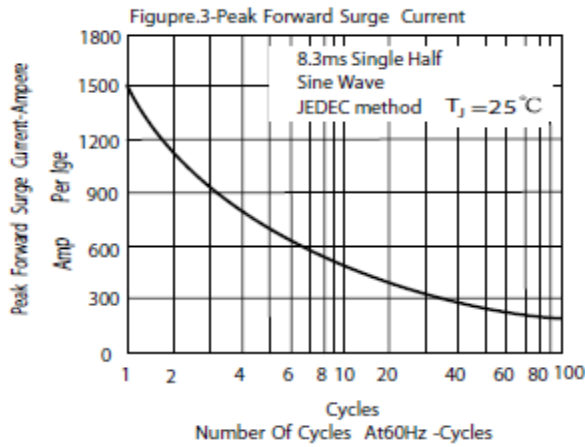
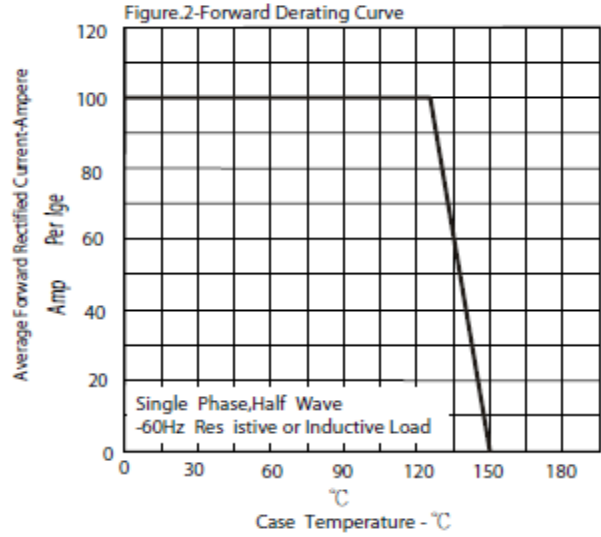
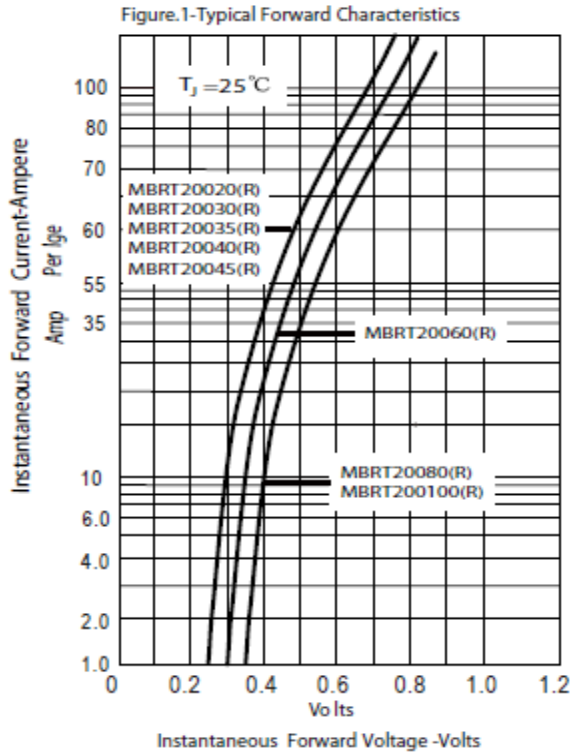
Parameter	Symbol	Conditions	MBRT20045(R)	MBRT20060(R)	MBRT20080(R)	MBRT200100(R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		45	60	80	100	V
RMS reverse voltage	$V_{RMS}$		32	42	56	70	V
DC blocking voltage	$V_{DC}$		45	60	80	100	V
Operating temperature	$T_j$		-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$

Electrical characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MBRT20045(R)	MBRT20060(R)	MBRT20080(R)	MBRT200100(R)	Unit
Average forward current (per pkg)	$I_{F(AV)}$	$T_C = 125\text{ }^\circ\text{C}$	200	200	200	200	A
Peak forward surge current (per leg)	$I_{FSM}$	$t_p = 8.3\text{ ms}$ , half sine	1500	1500	1500	1500	A
Maximum instantaneous forward voltage (per leg)	$V_F$	$I_{FM} = 100\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	0.70	0.75	0.84	0.84	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	$I_R$	$T_j = 25\text{ }^\circ\text{C}$ $T_j = 100\text{ }^\circ\text{C}$ $T_j = 150\text{ }^\circ\text{C}$	1 10 30	1 10 30	1 10 30	1 10 30	mA

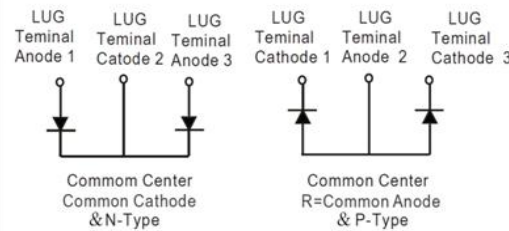
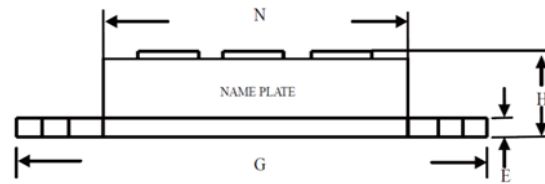
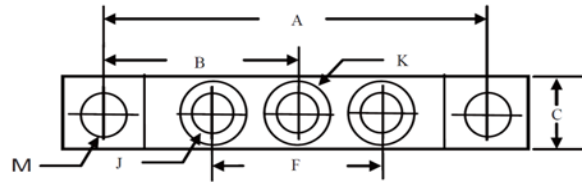
### Thermal characteristics

Thermal resistance, junction-case (per leg)	$R_{\theta JC}$		0.45	0.45	0.45	0.45	$^\circ\text{C/W}$
---	-----------------	--	------	------	------	------	--------------------



## Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	3.150	NOM	80.01	NOM
B	1.565	1.585	39.75	40.26
C	0.700	0.800	17.78	20.32
E	0.119	0.132	3.02	3.35
F	1.327	----	33.72	----
G	3.550	3.650	90.17	92.71
H	0.677	0.720	17.20	18.30
J	1/4-20 UNC FULL			
K	0.472	0.511	12	13
M	0.275	0.295	6.99	7.49
N	2.380	2.460	60.5	62.5

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Discrete Semiconductor Modules](#) category:*

*Click to view products by [GeneSiC Semiconductor](#) manufacturer:*

Other Similar products are found below :

[M252511FV](#) [DD260N12K-A](#) [DD380N16A](#) [DD89N1600K-A](#) [APT2X21DC60J](#) [APT58M80J](#) [B522F-2-YEC](#) [MSTC90-16](#) [25.163.0653.1](#)  
[25.163.2453.0](#) [25.163.4253.0](#) [25.190.2053.0](#) [25.194.3453.0](#) [25.320.4853.1](#) [25.320.5253.1](#) [25.326.3253.1](#) [25.326.3553.1](#) [25.330.1653.1](#)  
[25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#) [25.350.2053.0](#) [25.352.4753.1](#) [25.522.3253.0](#) [T483C](#) [T484C](#) [T485F](#) [T485H](#)  
[T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#) [25.326.4253.1](#) [25.330.0953.1](#)  
[25.332.4353.1](#) [25.350.1653.0](#) [25.350.2453.0](#) [25.352.1453.0](#) [25.352.1653.0](#) [25.352.2453.0](#) [25.352.5453.1](#) [25.522.3353.0](#) [25.602.4053.0](#)  
[25.640.5053.0](#)